

# PSMN2R0-60PS

N-channel 60 V 2.2 mΩ standard level MOSFET in TO-220
4 October 2012

Product data sheet

### 1. Product profile

#### 1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### 1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	120	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 12	[2]	-	1.8	2.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13		-	3	3.5	mΩ
Dynamic chara	Dynamic characteristics						
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 75 A; $V_{DS}$ = 30 V;		-	32	45	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 14; Fig. 15		-	137	192	nC



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche rug	gedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 $\Omega$ ; Unclamped	-	-	913	mJ

- [1] Continuous current limited by package[2] Measured 3 mm from package.

# **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	704	
3	S	source		G—U: 4
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

# **Ordering information**

Table 3. **Ordering information** 

Type number	Package					
	Name	Description	Version			
PSMN2R0-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

# **Marking**

Table 4. **Marking codes** 

Type number	Marking code
PSMN2R0-60PS	PSMN2R0-60PS

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	[1]	-	120	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	120	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	1135	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	338	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dra	in diode					
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1135	Α
Avalanche	ruggedness	1	-1	-		
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 Ω; Unclamped		-	913	mJ

<sup>[1]</sup> Continuous current limited by package

#### N-channel 60 V 2.2 m $\Omega$ standard level MOSFET in TO-220

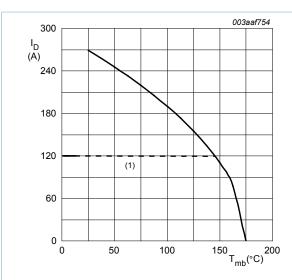


Fig. 1. Continuous drain current as a function of mounting base temperature.

 $V_{\it GS} \ge 10~{
m V};$  (1) Capped at 120 A due to package

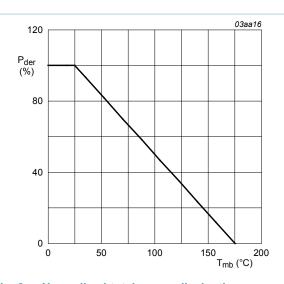


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \,\%$$

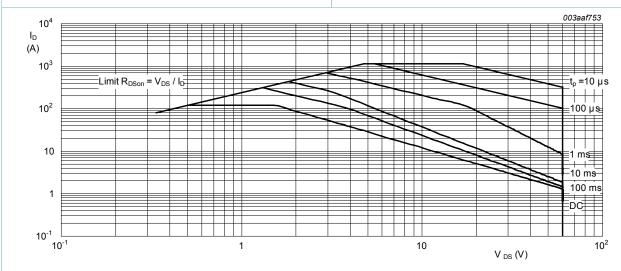


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse; Capped at 120 A due to package

#### 6. Thermal characteristics

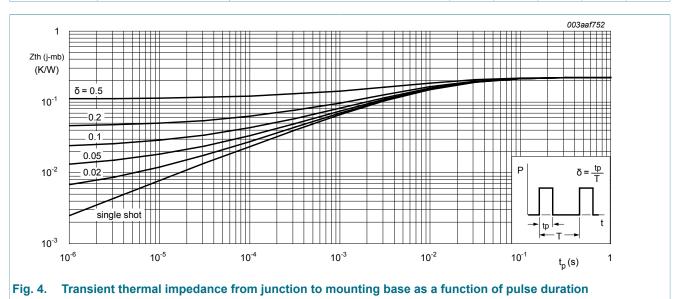
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.22	0.44	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics		<u> </u>		'		
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		54	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 10		1	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 11; Fig. 10		2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10		-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.03	10	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C		-	-	500	μΑ
GSS	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		-	-	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 12	[1]	-	1.8	2.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13		-	4.3	5.1	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13	-	3	3.5	mΩ
$R_G$	gate resistance	f = 1 MHz	0.45	0.9	1.8	Ω
Dynamic ch	naracteristics	1	'			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	137	192	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	129	181	nC
$Q_{GS}$	gate-source charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V	-	48	68	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	29	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	19	-	nC
$Q_{GD}$	gate-drain charge		-	32	45	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 30 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	5.7	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	9997	13500	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	1210	1640	pF
C <sub>rss</sub>	reverse transfer capacitance		-	594	835	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_{L}$ = 0.4 $\Omega$ ; $V_{GS}$ = 10 V;	-	42	63	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; I_D = 75 A$	-	56	84	ns
$t_{d(off)}$	turn-off delay time		-	115	173	ns
t <sub>f</sub>	fall time		-	49	74	ns
Source-drai	in diode		,			
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	8.0	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 30 V	-	57	75	ns
Q <sub>r</sub>	recovered charge	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 30 V	-	80	104	nC

<sup>[1]</sup> Measured 3 mm from package.

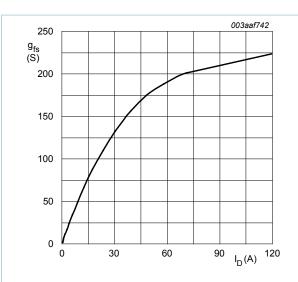


Fig. 5. Forward transconductance as a function of drain current; typical values



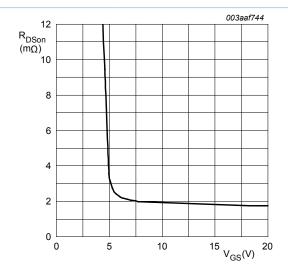


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
 °C;  $I_D = 25$  A

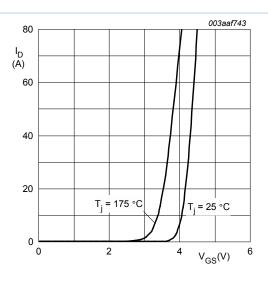


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

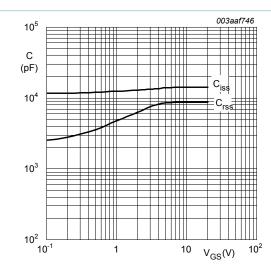


Fig. 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

$$V_{DS} = 0 \text{ V; } f = 1 \text{ MHz}$$

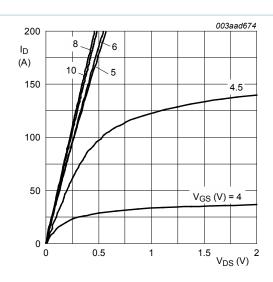


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values



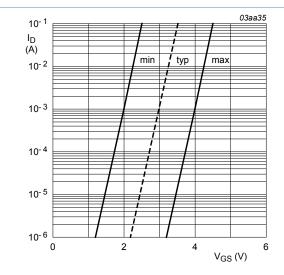


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25\,^{\circ}C; V_{DS} = 5V$$

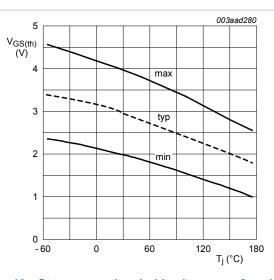


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

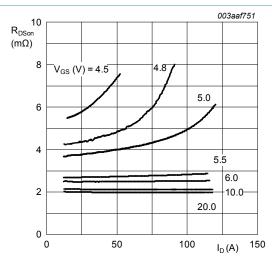
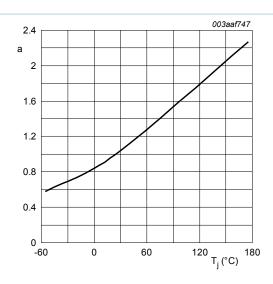


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25\,^{\circ}C$$



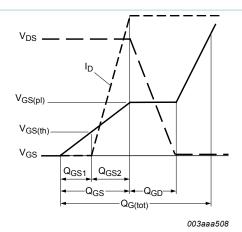
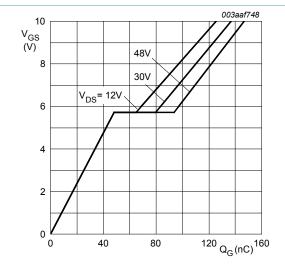
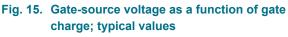


Fig. 14. Gate charge waveform definitions

Fig. 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
 °C;  $I_D = 25$  A





$$T_j = 25$$
 °C;  $I_D = 75$  A

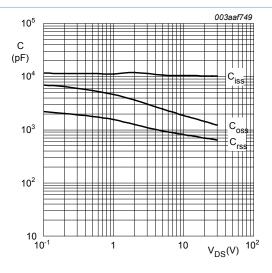


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$$

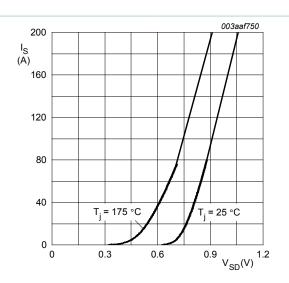
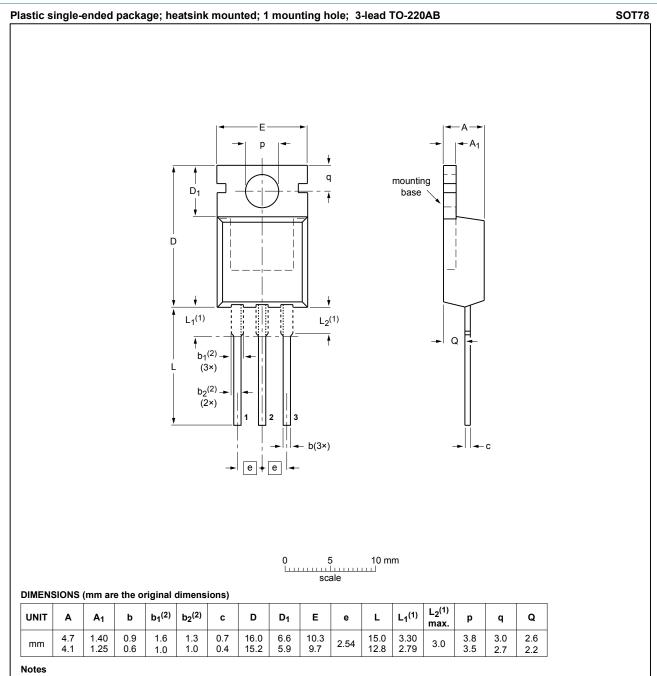


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0 \text{ V}$$

## 8. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

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#### N-channel 60 V 2.2 m $\Omega$ standard level MOSFET in TO-220

### 10. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	4
7	Characteristics	5
8	Package outline	11
9	Legal information	12
9.1	Data sheet status	12
9.2	Definitions	12
9.3	Disclaimers	12
9.4	Trademarks	13

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